# MPSA12

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# **NPN Darlington Transistor**

- This device is designed for applications requiring extremely high WWW.100Y.COM.
- current gain at currents to 1.0A.
- Sourced from process 05.

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• See MPSA14 for characteristics.

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1. Emitter 2. Base 3. Collector

TO-92

# Absolute Maximum Ratings \* T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CES</sub>	Collector-Emitter Voltage	20	V
V <sub>CBO</sub>	Collector-Base Voltage	20	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
I <sub>C</sub>	Collector Current - Continuous	1.2	А
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 ~ +150	°C

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

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1. These ratings are based on a maximum junction temperature of 150 degrees C.

These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# Electrical Characteristics TA=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Chara	cteristics	DIAT MAN	. Vool	COm	Wn.	
V <sub>(BR)CES</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$	20	100	1.1	V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 15V, I_E = 0$	100		100	nA
I <sub>CES</sub>	Emitter Cutoff Current	$V_{CB} = 15V, I_{C} = 0$	N	V.C.	100	nA
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 10V, I_{C} = 0$	W.10	-16	100	nA
On Chara	cteristics *	W WIN	1	10X.~	Mo	L.M.
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 5.0V, I_{C} = 10mA$	20,000	N.		Mr.
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.01mA	W.	100	1.0	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$I_{C} = 10 \text{mA}, V_{CE} = 5.0 \text{V}$		1007	1.4	V
Pulse Test: Pu	ulse Width ≤ 300µs, Duty Cycle ≤ 2.0%					

# Thermal Characteristics T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	200	°C/W

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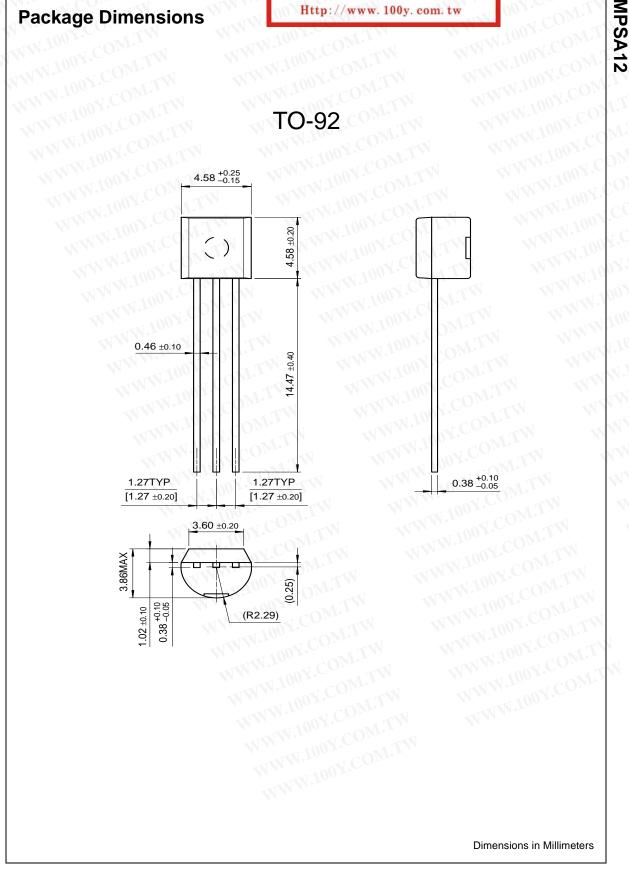
# Package Dimensions

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### **Definition of Terms**

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